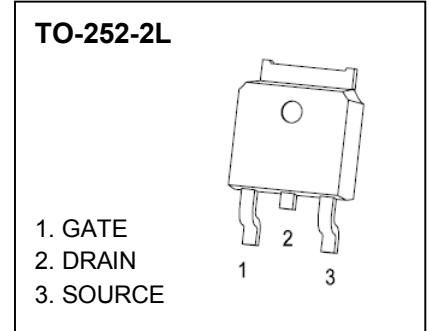




TO-252-2L Plastic-Encapsulate MOSFETS

CJU30N10 N-Channel Power MOSFET

V_{(BR)DSS}	R_{DS(on)MAX}	I_D
100V	31mΩ@10V	30A



DESCRIPTION

This advanced high voltage MOSFET is designed to stand high energy in the avalanche mode and switch efficiently. This new high energy device also offers a drain-to-source diode fast recovery time.

Designed for high voltage, high speed switching applications such as power supplies, converters, power motor controls and bridge circuits.

FEATURES

- High density cell design for ultra low R_{DS(on)}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Special process technology for high ESD capability
- Excellent package for good heat dissipation

APPLICATIONS

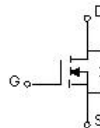
- Hard switched and high frequency circuits
- Uninterruptible power supply
- Power switching application

MARKING



CJU30N10= Device code
 Solid dot = Green molding compound device,
 if none, the normal device
 XXX=Date Code

EQUIVALENT CIRCUIT



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D	30	A
Pulsed Drain Current	I _{DM}	120	A
Single Pulsed Avalanche Energy	E _{AS} ⁽¹⁾	156	mJ
Power Dissipation	P _D	1.25	W
Thermal Resistance from Junction to Ambient	R _{θJA}	100	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 ~+150	°C
Lead Temperature for Soldering Purposes(1/8" from case for 10s)	T _L	260	°C

(1).E_{AS} condition: V_{DD}=50V,L=0.5mH, R_G=25Ω, Starting T_J = 25°C

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^\circ\text{C}$ unless otherwise specified

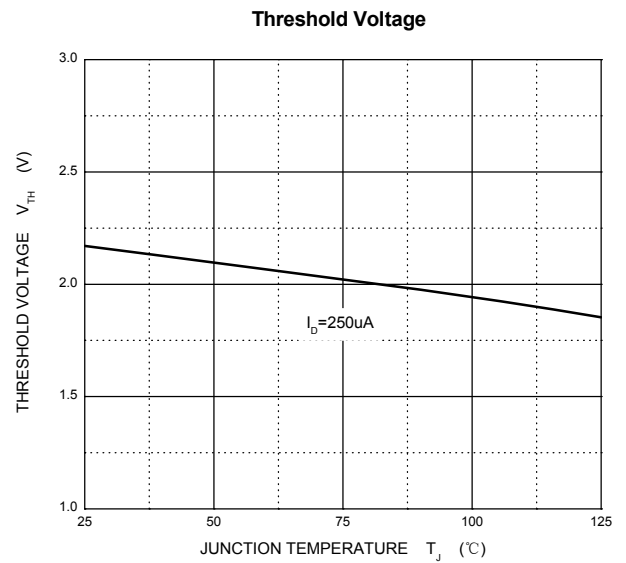
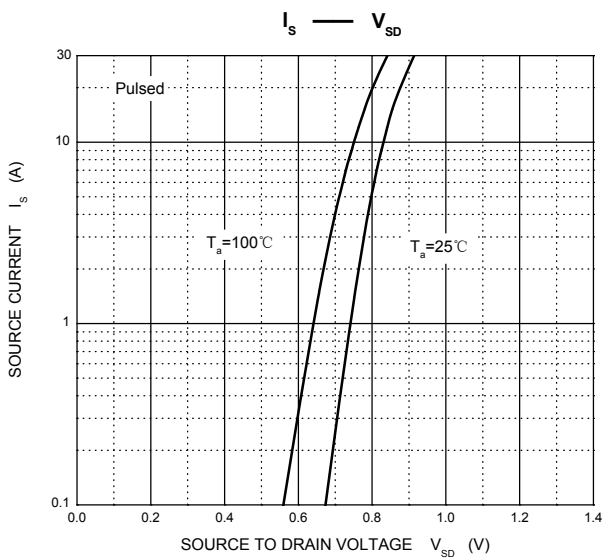
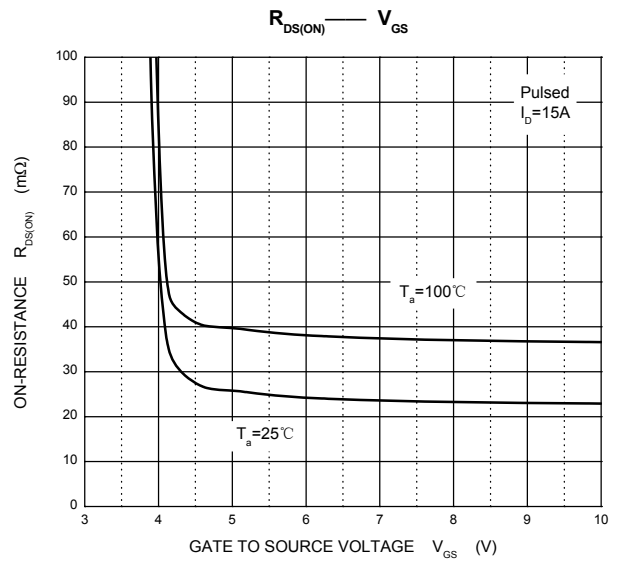
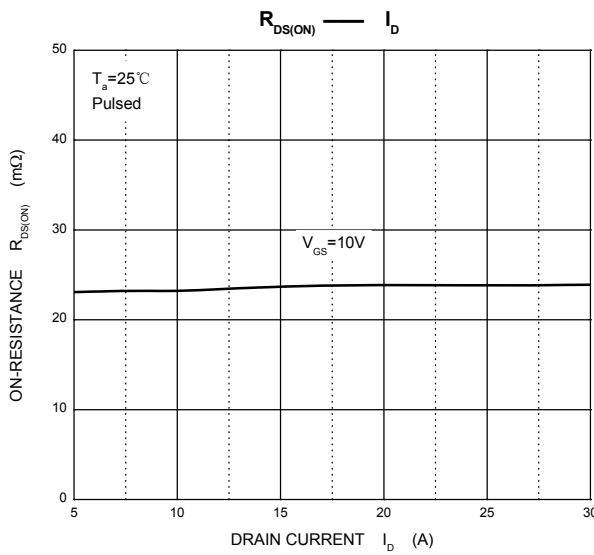
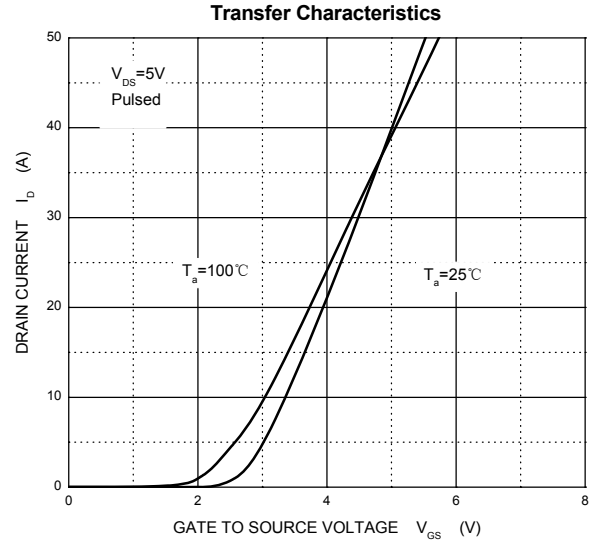
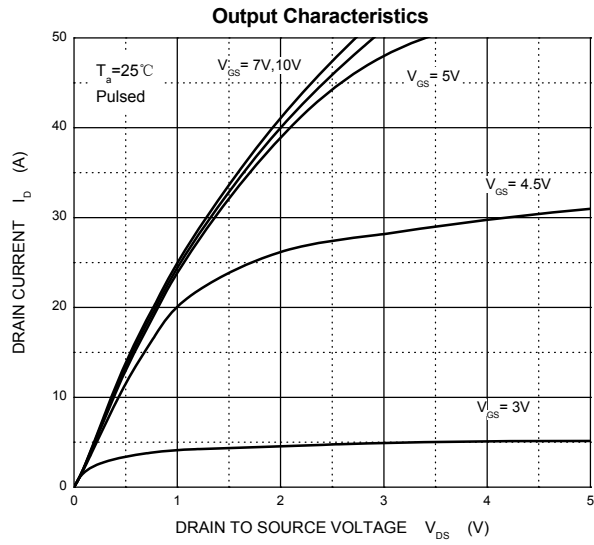
ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
On characteristics (note1)						
Gate-threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.3	2.1	2.5	V
Static drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 15A$		24	31	m Ω
Forward transconductance	g_{fs}	$V_{DS} = 5V, I_D = 10A$		15		S
Dynamic characteristics (note 2)						
Input capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1MHz$		2000		pF
Output capacitance	C_{oss}			300		
Reverse transfer capacitance	C_{rss}			250		
Switching characteristics (note 2)						
Total gate charge	Q_g	$V_{DS} = 50V, V_{GS} = 10V,$ $I_D = 10A$		39		nC
Gate-source charge	Q_{gs}			8		
Gate-drain charge	Q_{gd}			12		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30V, V_{GS} = 10V, R_G =$ $3.0\Omega, I_D = 2A, R_L = 5\Omega$		7		ns
Turn-on rise time	t_r			7		
Turn-off delay time	$t_{d(off)}$			29		
Turn-off fall time	t_f			7		
Drain-Source Diode Characteristics						
Drain-source diode forward voltage(note1)	V_{SD}	$V_{GS} = 0V, I_S = 15A$			1.2	V
Continuous drain-source diode forward current	I_S				30	A
Pulsed drain-source diode forward current	I_{SM}				120	A

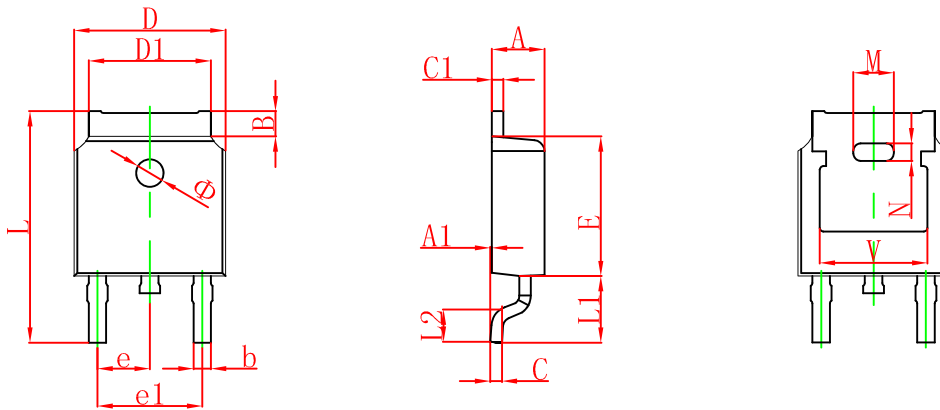
Notes:

1. Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
2. Guaranteed by design, not subject to production.

Typical Characteristics

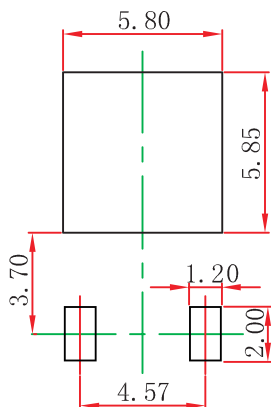


TO-252(4R)-2L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A1	0.000	0.100	0.000	0.004
B	0.800	1.400	0.031	0.055
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
c1	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
E	6.000	6.200	0.236	0.244
e	2.286 TYP.		0.090 TYP.	
e1	4.327	4.727	0.170	0.186
M	1.778REF.		0.070REF.	
N	0.762REF.		0.018REF.	
L	9.800	10.400	0.386	0.409
L1	2.9REF.		0.114REF.	
L2	1.400	1.700	0.055	0.067
V	4.830 REF.		0.190 REF.	
Φ	1.100	1.300	0.043	0.051

TO-252(4R)-2L Suggested Pad Layout



Note:

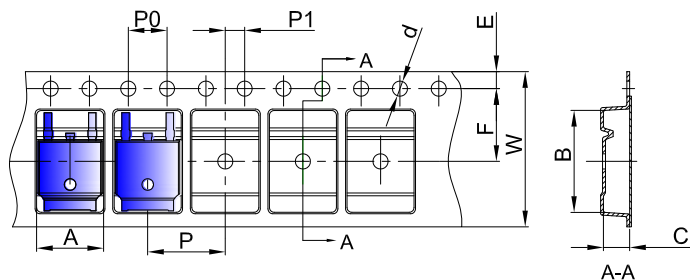
1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

NOTICE

JCET reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JCET does not assume any liability arising out of the application or use of any product described herein.

To-252(4R)-2L Tape and Reel

TO-252 Embossed Carrier Tape

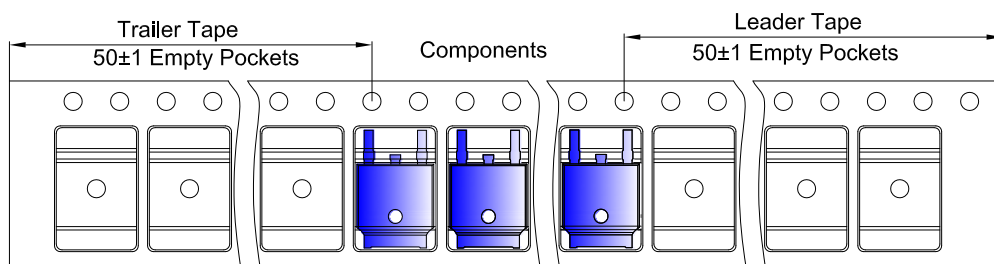


Packaging Description:

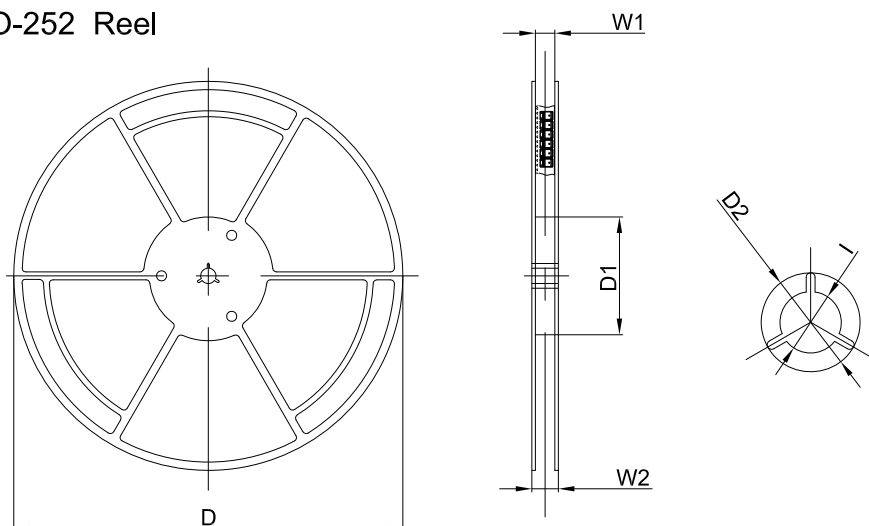
TO-252 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 25,00 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
TO-252	6.90	10.50	2.70	Ø1.55	1.75	7.50	4.00	8.00	2.00	16.00

TO-252 Tape Leader and Trailer



TO-252 Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	W1	W2	I
13"Dia	330.00	100.00	Ø21.00	16.40	21.00	Ø13.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13inch	2,500 pcs	340×336×29	25,000 pcs	353×346×365	